

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

Claims 1-14 (canceled).

Claim 15 (currently amended): A copper alloy sputtering target according to claim [3] 30, wherein a recrystallization temperature of said target is 365°C or less.

Claim 16 (currently amended): A copper alloy sputtering target according to claim [15] 30, wherein said target contains 1wtppm or less of oxygen.

Claim 17 (canceled).

Claim 18 (currently amended): A copper alloy sputtering target according to claim [1] 33, wherein a recrystallization temperature of said target is 365°C or less.

Claims 19-29 (canceled).

Claim 30 (previously presented): A copper alloy sputtering target for forming wiring of a semiconductor element, consisting of copper, 0.5 to 4.0wt% of Al, 5wtppm or less of oxygen, and an amount of Si to improve oxidation resistance, said amount of Si not exceeding 0.5wtppm,

and said target having an average crystal grain size of 0.1 to 60 $\mu$ m and an average grain size variation of within  $\pm 20\%$ .

Claim 31 (previously presented): A copper alloy sputtering target according to claim 30, wherein said amount of Si is 0.19wtppm to 0.41wtppm.

Claim 32 (previously presented): A copper alloy sputtering target according to claim 30, wherein said copper is high purity copper having a purity of 6N (99.9999%) or higher.

Claim 33 (previously presented): A copper alloy sputtering target for forming wiring of a semiconductor element, consisting of copper, 0.5 to 4.0wt% of Al, 5wtppm or less of oxygen, one or more selected from among Sb, Zr, Ti, Cr, Ag, Au, Cd, In and As in a total amount of 1.0wtppm or less, and an amount of Si to improve oxidation resistance, said amount of Si not exceeding 0.5wtppm, and said target having an average crystal grain size of 0.1 to 60 $\mu$ m and an average grain size variation of within  $\pm 20\%$ .

Claim 34 (previously presented): A copper alloy sputtering target according to claim 33, wherein said total amount of one or more selected from among Sb, Zr, Ti, Cr, Ag, Au, Cd, In and As is 0.24wtppm to 0.44wtppm.

Claim 35 (previously presented): A copper alloy sputtering target according to claim 34, wherein said amount of Si is 0.19wtppm to 0.41wtppm.

Claim 36 (previously presented): A copper alloy sputtering target according to claim 35, wherein said copper is high purity copper having a purity of 6N (99.9999%) or higher.